



# CHENMKO ENTERPRISE CO.,LTD

**CH801H-30PT**

*Lead free devices*

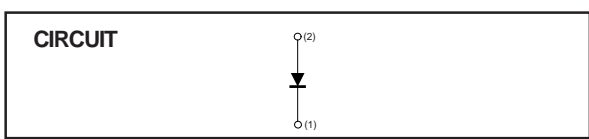
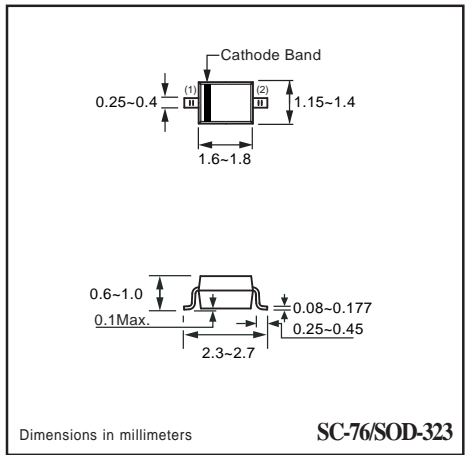
**SURFACE MOUNT**  
**SCHOTTKY BARRIER DIODE**  
**VOLTAGE 30 Volts CURRENT 0.1 Ampere**

**APPLICATION**  
 \* Low power rectification

**FEATURE**  
 \* Small surface mounting type. (SC-76/SOD-323)  
 \* Low VF. (VF=0.37V Typ. at 100mA)  
 \* High reliability

**CONSTRUCTION**  
 \* Silicon epitaxial planar

**MARKING**  
 \* JS



**MAXIMUM RATINGS** ( At TA = 25°C unless otherwise noted )

RATINGS	SYMBOL	CH801H-30PT	UNITS
Maximum Recurrent Peak Reverse Voltage	VRRM	30	Volts
Maximum RMS Voltage	VRMS	21	Volts
Maximum DC Blocking Voltage	VDC	30	Volts
Maximum Average Forward Rectified Current	Io	0.1	Amps
Peak Forward Surge Current at 10 mSec single half sine-wave	IFSM	1.0	Amps
Typical Junction Capacitance between Terminal (Note 1)	CJ	6.0	pF
Maximum Operating Temperature Range	TJ	-40 to +125	°C
Storage Temperature Range	TSTG	-55 to +125	°C

**ELECTRICAL CHARACTERISTICS** ( At TA = 25°C unless otherwise noted )

CHARACTERISTICS		SYMBOL	CH801H-30PT	UNITS
Maximum Instantaneous Forward Voltage	at IF= 100mA	VF	0.45	Volts
	at IF= 1.0 mA		0.37	Volts
Maximum Average Reverse Current at VR= 30V		IR	1.0	uAmps

NOTES : 1. Measured at 1.0 MHz and applied reverse voltage of 10.0 volts.  
 2. ESD sensitive product handling required.

2002-5

## RATING CHARACTERISTIC CURVES ( CH801H-30PT )

FIG. 1 - FORWARD CHARACTERISTICS

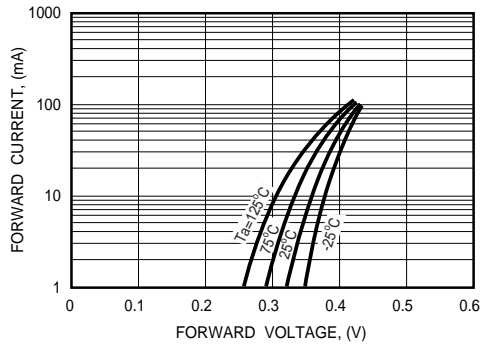


FIG. 2 - REVERSE CHARACTERISTICS

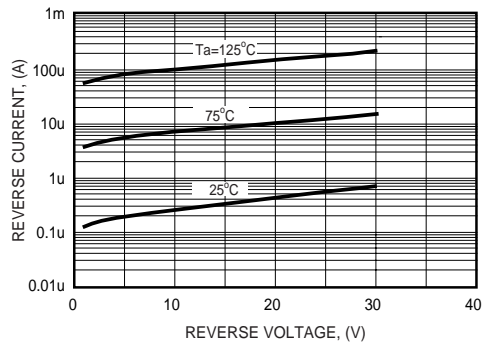


FIG. 3 - TYPICAL JUNCTION CAPACITANCE

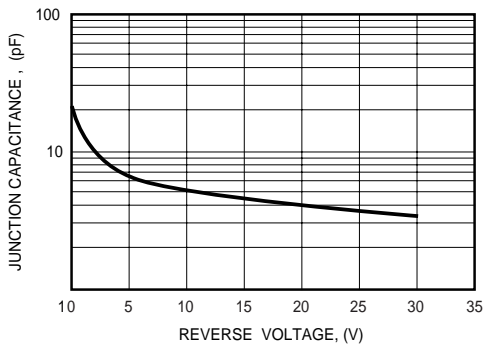


FIG. 4 - TYPICAL FORWARD CURRENT DERATING CURVE

